

FORM PTO-1449

LIST OF PATENTS AND PUBLICATIONS FOR  
APPLICANT'S INFORMATION DISCLOSURE  
STATEMENT

(Use several sheets if necessary)

ATTY. DOCKET NO.

10007799-1

SERIAL NO.

APPLICANT

Xia Sheng et al

FILING DATE

04/30/2001

GROUP

10007799-1 U.S. PTO  
09/845845



REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS
JH	1A	6,162,716	12/19/2000	Chen-Hua Yu et al	438	592
	1B	6,136,684	10/24/2000	Nobuhiko Sato et al	438	624
	1C	6,187,604	02/13/2001	Terry L. Gilton	438	20
	1D	5,990,605	11/23/1999	Takamasa Yoshikawa et al	313	310
	1E	5,894,189	04/13/1999	Kiyohide Ogasawara et al	313	310
	1F	5,863,232	01/26/1999	Seok Soo Lee	445	24
	1G	5,556,530	09/17/1996	Walter Finkelstein et al	205	122
	1H	5,296,388	03/22/1994	Shuichi Kameyama et al	437	31
	1I					
	1J					
	1K					

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	TRANSLATION	
							YES	NO
JH	1L	EP1047095A2	10/25/2000	Yoshifumi Watabe et al	H01J	1/30	x	
	1M	EP1026721A1	08/09/2000	Takashi Hatai et al	H01J	1/30	x	
	1N	EP1003195A2	05/24/2000	Takashi Hatai et al	H01J	1/30	x	
	1O	EP0913849A2	05/06/1999	Takuya Komoda et al	H01J	1/30	x	
	1P							

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

JH	1Q	Jean-Claude Vial & Jacques Derrien - "Porous Silicon Science and Technology" - February 1994 pages 32-53
	1R	Selena Chan & Philippe M. Fauchet - "Tunable, Narrow, and Directional Luminescence From Porous Silicon Light Emitting Devices" - July 1999 - pages 274-276
	1S	Xia Sheng, Hideki Koyama & Nobuyoshi Koshida - "Efficient Surface-Emitting Cold Cathodes Based on Electroluminescent Porous Silicon Diodes" - March/April 1998 - pages 793-795

EXAMINER

*[Signature]*

DATE CONSIDERED

4/22/03

FORM PTO-1449

LIST OF PATENTS AND PUBLICATIONS FOR  
APPLICANT'S INFORMATION DISCLOSURE  
STATEMENT

(Use several sheets if necessary)

ATTY. DOCKET NO.

10007799-1

SERIAL NO.

APPLICANT

Xia Sheng et al

FILING DATE

04/30/2001

GROUP

1c997 U.S. PTO

09/845845



04/30/01

## REFERENCE DESIGNATION

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS
	1A					
	1B					
	1C					
	1D					
	1E					
	1F					
	1G					
	1H					
	1I					
	1J					
	1K					

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	TRANSLATION	
							YES	NO
	1L							
	1M							
	1N							
	1O							
	1P							

## OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)

<i>gr</i>	1Q	N. Koshida, X. Sheng & T. Komoda - "Quasiballistic Electron Emission From Porous Silicon Diodes" - May 1999 - pages 371-376
<i>gr</i>	1R	Paul Snow, Yi Zhou, Philip Allcock, John Pottage, Jonathan Knight & Philip Russell - "Porous Silicon" - April 12, 2001 - pages 1-2
	1S	

EXAMINER

DATE CONSIDERED

4/22/03

PTO JOB  
MAR 25 2002  
PATENT & TRADEMARK OFFICE

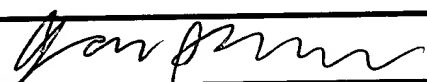
Please type a plus sign (+) inside this box → ☐

PTO/SB/08B (08-00)  
Approved for use through 10/31/2002. OMB 0651-0031  
U. S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE  
Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO		<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		Application Number	09/845,945
		Filing Date	Apr 30, 2001
		First Named Inventor	Poh Boon Phua
		Group Art Unit	2874
		Examiner Name	
Sheet 1 of 1	Attorney Docket Number	1085-022-PWH	

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
gk		US Patent Application No. 09/963,181 "An Apparatus for Generating Laser Radiation" filed 9/25/01; 18 pages	
		BOWMAN et al; "High Power Diode Pumped Micron Lasers" SPIE Vol. 1865 pp 156 - 163; 1993	
		SHANNON et al; "High Average Power Diode-Pumped Lasers Near 2 um" SPEI Vol. 1865; pp 164-173	
		RUSTAD et al; "Low Threshold Laser-Diode Side-Pumped TM:YAG and TM:Ho:YAG Lasers" IEEE Jnl of Sel Topics in Quatum Electronics Vol 3 2/1997 8 pages	
		HONEA; "115-W TM:YAG Diode-Pumped Solid-State Laser"; IEEE Jnl of Sel Topics in Quatum Electronics Vol 33 9/1997 9 pages	
		JACKSON "Efficient Gain-Switched Operation of a TM-Doped Silica Fiber Laser" EEE Jnl of Sel Topics in Quatum Electron. Vol 3 /1998 11 pages	
		BOLLIG "2-W Ho:YAG Laser Intercavity Pumped by a Diode-Pumped Tm:YAG Laser" Optics Letters Vol 23 No 22 11/1998 3 pages	
✓		RUSTAD; Modeling of Laser-Pumped TM and HO Lasers Accounting for Upconversion and Bround State Depletion; IEEE Journal of Quant. El. V32, #9 9/1996; 12 pages	

RECEIVED  
APR - 1 2002  
TECHNOLOGY CENTER 2800

Examiner Signature		Date Considered	4/22/03
--------------------	-------------------------------------------------------------------------------------	-----------------	---------

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Unique citation designation number. <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U. S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, DC 20231.